TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSII)

# 2SK3389

Switching Regulator, DC-DC Converter Applications Motor Drive Applications

- Low drain-source ON resistance:  $R_{DS}$  (ON) = 3.8 m $\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 70 \text{ S} (typ.)$
- Low leakage current:  $I_{DSS} = 100 \ \mu A (V_{DS} = 30 \ V)$
- Enhancement-mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

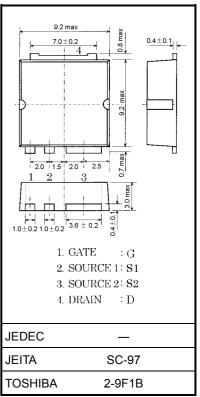
#### Maximum Ratings (Tc = 25°C)

**Thermal Characteristics** 

Thermal resistance, channel to case

Characteristics

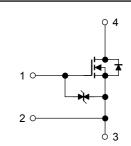
Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	30	V	
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		V <sub>DGR</sub>	30	V	
Gate-source voltage		V <sub>GSS</sub>	±30	V	
Drain current	DC (Note 1)	Ι <sub>D</sub>	75	А	
	Pulse (Note 1)	I <sub>DP</sub>	300	~	
Drain power dissipation		PD	125	W	
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	731	mJ	
Avalanche current		I <sub>AR</sub>	75	А	
Repetitive avalanche energy (Note 3)		E <sub>AR</sub>	12.5	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	



Weight: 0.74 g (typ.)

#### Notice:

Please use the S1 pin for gate input signal return. Make sure that the main current flows into S2 pin.



Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2:  $V_{DD} = 25 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}$  (initial), L = 95  $\mu$ H, I<sub>AR</sub> = 75 A, R<sub>G</sub> = 25  $\Omega$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

Symbol

Rth (ch-c)

Max

1.00

Unit

°C/W

This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm

### Electrical Characteristics (Note 4) (Tc = 25°C)

Cha	aracteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rrent	I <sub>GSS</sub>	$V_{GS}=\pm 25~V,~V_{DS}=0~V$	_		±10	μA
Drain cut-off curr	ent	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			100	μA
Drain-source bre	akdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30			V
Gate threshold ve	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2.0		4.0	V
Drain-source ON	resistance	R <sub>DS (ON)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 38 \text{ A}$		3.8	5.0	mΩ
Forward transfer	admittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 38 \text{ A}$	35	70	_	S
Input capacitance	e	C <sub>iss</sub>			3530	_	
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		570	_	pF
Output capacitance		C <sub>oss</sub>		_	1870		
Switching time	Rise time	tr	$V_{GS} \stackrel{10}{}_{0}V \stackrel{I}{\downarrow} \stackrel{I}{\downarrow} \stackrel{I}{}_{D} = 38 \text{ A}$		10	_	ns
	Turn-on time	t <sub>on</sub>		_	25	_	
	Fall time	t <sub>f</sub>		_	20	_	
	Turn-off time	t <sub>off</sub>	Duty $\leq$ 1%, t <sub>w</sub> = 10 µs	_	65	_	
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD}\simeq 24$ V, $V_{GS}=10$ V, $I_{D}=75$ A $^{\circ}$		62		nC
Gate-source charge		Q <sub>gs</sub>		_	43	_	
Gate-drain ("miller") charge		Q <sub>gd</sub>			19		

Note 4: Please connect the S1 pin and S2 pin, and then ground the connected pin. (However, while switching times are measured, please don't connect and ground it.)

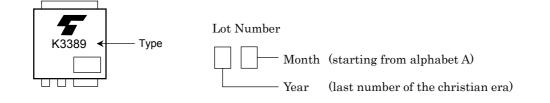
#### Source-Drain Ratings and Characteristics (Note 5) (Tc = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1, Note 5)	I <sub>DR</sub> 1	_	_	_	75	А
Pulse drain reverse current (Note 1, Note 5)	I <sub>DRP</sub> 1	—	_		300	А
Continuous drain reverse current (Note 1, Note 5)	I <sub>DR</sub> 2	—	_		1	А
Pulse drain reverse current (Note 1, Note 5)	I <sub>DRP</sub> 2	_	_		4	A
Forward voltage (diode)	V <sub>DS2F</sub>	$I_{DR}$ 1 = 75 A, $V_{GS}$ = 0 V	—	—	-1.5	V
Reverse recovery time	t <sub>rr</sub>	$I_{DR} = 75 \text{ A}, V_{GS} = 0 \text{ V},$	—	120		ns
Reverse recovery charge	Qrr	dI <sub>DR</sub> /dt = 50 A/μs	_	180	_	nC

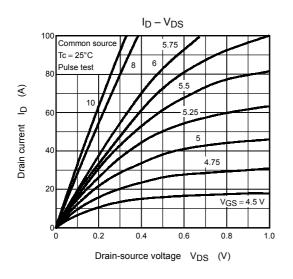
Note 5: drain, flowing current value between the S2 pin, open the S1 pin drain, flowing current value between the S1 pin, open the S2 pin

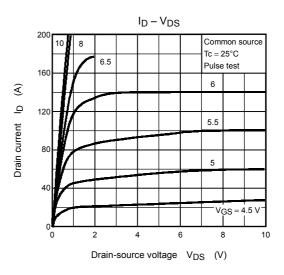
Unless otherwise specified, please connect the S1 and S2 pins, and then ground the connected pin.

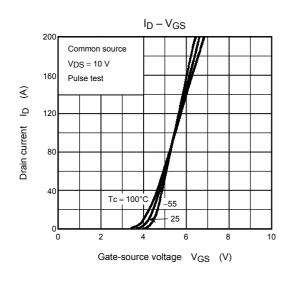
#### Marking

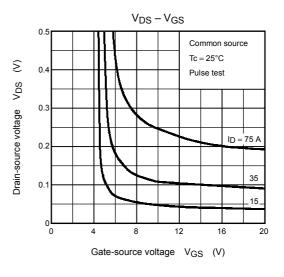


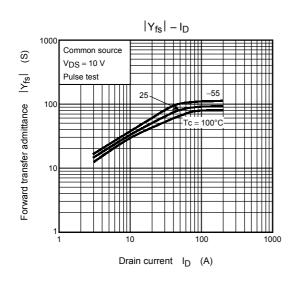
## **TOSHIBA**

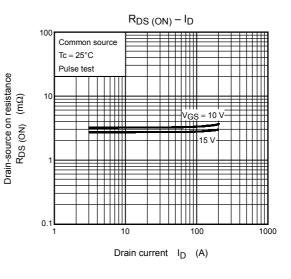


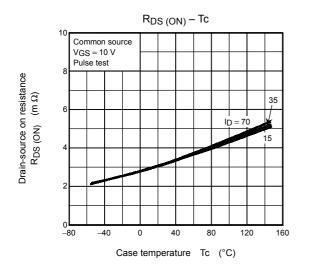


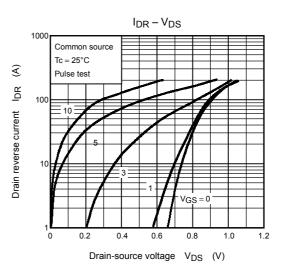


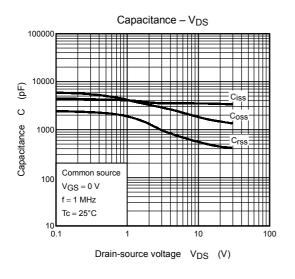


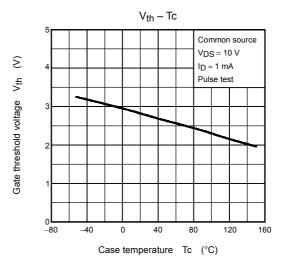


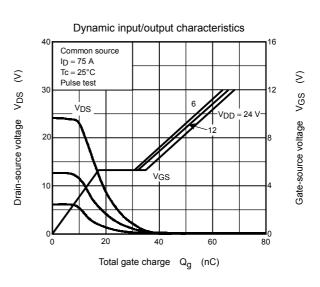




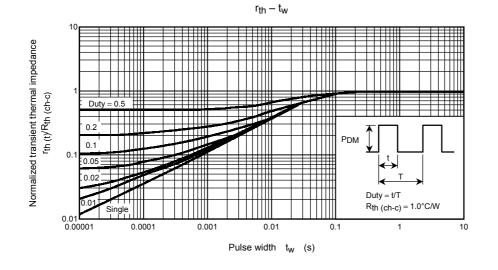


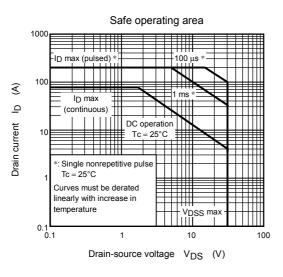


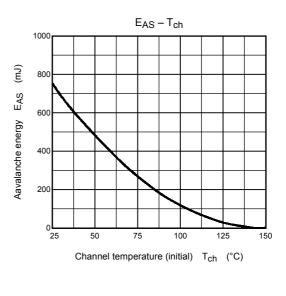


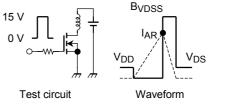


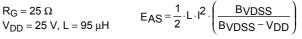
PD-TC  $P_D$ -TC  $P_D$ -TC











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